The recoveries of PL were between 90—104% and the coefficients of variation were between 1.21—4.30%, while the recovery of PLP added to human serum was only 63.3%, suggesting that some amount of PLP might be precipitated with denaturated protein. It is, therefore, favorable to determine PLP as PL after hydrolysis in order to obtain higher recovery. The enzymatic hydrolysis of PLP was examined with the same procedure reported by Takanashi, et al.7 As shown in Table I, the recovery of PLP added to serum increased from 63.3% to 91.6% by using acid phosphatase solution obtained from potato. The separately determination of PL and PLP would be achieved by this method after SM-cellulose column separation with 0.01n acetic acid as described by Yamada, et al.5)

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## Electron Spin Resonance Study of γ-Irradiated H<sub>2</sub>SO<sub>4</sub>-SiO<sub>2</sub> System

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The  $SO_4$ - radicals was formed in  $\gamma$ -irradiated  $H_2SO_4$ -SiO<sub>2</sub> system at  $-196^\circ$ . The formation of the  $SO_3$ - radicals are accompanied when  $\gamma$ -irradiation is carried out after heat-treatment at  $500^\circ$ , indicating that  $H_2SO_4$  on  $SiO_2$  is stable even at  $500^\circ$ .

The  $SO_4^-$  radicals are known to be formed in  $\gamma$ -irradiated sulfuric acid glasses.<sup>2–5)</sup> On the other hand, the  $SO_3^-$  and  $SO_2^-$  radicals are formed besides the  $SO_4^-$  radicals in irradiated sulfates. However, the kinds of the radicals change with the sorts of the sulfates and irradiation in these cases.<sup>6–10)</sup>

In the present study, the electron spin resonance (ESR) spectra of the  $\gamma$ -irradiated  $H_2SO_4$ -SiO<sub>2</sub> system were measured and compared with the above-mentioned reports. In addition, the effects of heat-treatment and the absorption of  $H_2O$  were examined.

The property of silica as a solid acid is well known. The silica treated with H<sub>2</sub>SO<sub>4</sub> behaves as an another acid which shows a catalytic effect, for example, on the cracking of petroluem.<sup>11)</sup>

<sup>1)</sup> Location: 2-2-1, Oshika, Shizuoka.

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<sup>3)</sup> P.N. Moothy and J.J. Weiss, in "Solvated Electron," Advances in Chemistry Series, No. 50, American Chemical Society, Washington, D.C., 1965, p. 180.

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<sup>6)</sup> J.R. Morton, D.M. Bishop, and M. Randic, J. Chem. Phys., 45, 1885 (1966).

<sup>7)</sup> V.V. Gromov and J.R. Morton, Can. J. Chem., 44, 527 (1966).

<sup>8)</sup> N. Hariharan and J. Sobhanadri, Mol. Phys., 17, 507 (1969).

<sup>9)</sup> K. Aiki and K. Hukuda, J. Phys. Soc. Japan, 22, 663 (1967).

<sup>10)</sup> I. Suzuki and R. Abe, J. Phys. Soc. Japan, 30, 586 (1971).

<sup>11)</sup> K. Tanabe and T. Takeshita, "San-Enki Syokubai," Sangyo Tosyo, Tokyo, 1966, p. 213.

On the other hand,  $\gamma$ -irradiation increases the acidity of clay.<sup>12)</sup> Therefore, it is interesting to study what kind of radical is formed in the  $H_2SO_4$ -SiO<sub>2</sub> system.

## Experimental

 $H_2SO_4$  (Wako Pure Chemical Industries, Ltd.) and 100 mesh  $SiO_2 \cdot xH_2O$  (Mallinckrodt Chemical Works) are guaranteed and analytical reagents, respectively.

 $SiO_2 \cdot xH_2O$  was immersed in 50% sulfuric acid and boiled for 5 hours. The mixture was cooled to room temperature and the  $SiO_2 \cdot xH_2O$  was washed 5 times with distilled water, and then dried in a desiccator. The sample is described hereinafter as  $H_2SO_4$ - $SiO_2$ .

Gamma irradiation from a  $^{60}$ Co source was carried out at a dose rate of about  $5\times10^4$  R/hr for 17 hours at  $-196^{\circ}$ .

ESR spectra were measured with a Japan Electron Optics Laboratory Model JES-3BS.X Spectrometer (X-band) with 100 kHz field modulation.

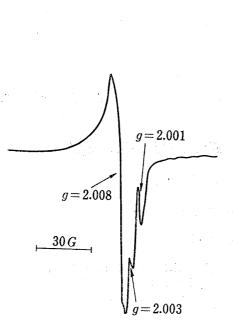


Fig. 1. ESR Spectrum of SiO  $\cdot xH_2O$  at  $-196^\circ$ ,  $\gamma$ -Irradiated after Heattreatment at 500° (gain  $2.0 \times 100$ )

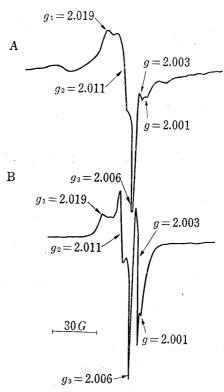


Fig. 2. ESR Spectra of  $\gamma$ -Irradiated  $H_2SO_4$ -SiO<sub>2</sub> at  $-196^\circ$ , (A): Non-heat-treated (gain  $6.3\times10$ ), (B): Heat-treated at  $500^\circ$  (gain  $1.4\times100$ )

## Results and Discussion

Figure 1 shows the ESR spectrum of  $SiO_2 \cdot xH_2O$   $\gamma$ -irradiated at  $-196^\circ$  after heat-treatment at  $500^\circ$  for 5 hours. It is well known that the spectra of silica depends on the ways of preparation and impurities. The spectrum in Fig. 1 consists of three absorption lines and is very similar to that reported by Kinell, et al.<sup>13)</sup> According to ref. 13, the absorption at g=2.001 appearing also in  $\gamma$ -irradiated quartz and fused silica is attributed to the electrons trapped in an oxygen vacancy in the  $SiO_2$  network. The absorption at g=2.003 is probably due to trapped electrons, but the site is not clear. The strong and asymmetric absorption centered at g=2.008 is attributed to the holes trapped in a non-bridging oxygen formed by hydrogen

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rupture of the silanol group on the surface. These absorption lines almost disappeared when the sample was kept for a day at room temperature.

Figure 2-A shows the ESR spectrum of  $H_2SO_4$ -SiO<sub>2</sub> evacuated at room temperature and  $\gamma$ -irradiated at  $-196^\circ$ . Two lines at g=2.001 and g=2.003 are attributable to the trapped electrons as in the case of  $SiO_2 \cdot xH_2O$ . The strong absorption in the low field side differs from that of the hole trapped at the surface oxygen. If the spectrum comes from only one species, asymmetric line shape is due to the anisotropic g value ( $g_1=2.019$ ,  $g_2=2.011$ ,  $g_3=2.006$ ). The values are nearly equal to those of the  $SO_4$  radicals ( $g_1=2.0189$ ,  $g_2=2.0130$ ,  $g_3=2.0053$ ) formed in  $\gamma$ -irradiated frozen aqueous sulfuric acid glasses.<sup>3)</sup> These radicals disappeared when the sample was kept at room temperature for a day.

Figure 2-B shows the ESR spectrum of  $H_2SO_4$ –SiO<sub>2</sub>  $\gamma$ -irradiated and measured at  $-196^\circ$  after heat-treatment at 500° for 5 hours. The strong absorption line in the low field side is somewhat different from that in Fig. 2-A. However, the g values of the radicals are exactly equal. Furtheremore, the sample adsorbed  $H_2O$  in contact with the saturated vapor of  $H_2O$  at room temperature after heat-treatment at 500° and then  $\gamma$ -irradiated at  $-196^\circ$  shows an ESR spectrum very similar to that in Fig. 2-A with respect to the intensity and the line shape. These facts suggest that  $H_2SO_4$  on SiO<sub>2</sub> is stable even at 500° in contrast to  $H_2SO_4$  which decomposes at 290° and the difference between the spectra in Fig. 2-A and 2-B comes from the effect of adsorbed  $H_2O$ . Considering the facts that  $H_2SO_4$  is not destroyed by heat-treatment at 500° and the g values are equal, both absorptions in the low field side in Fig. 2-A and 2-B can be attributed to the  $SO_4$  radicals. The difference in line shape may be due to the change of the environment resulting from dehydration.

Besides the absorption of the  $SO_4^-$  radicals, a strong and sharp absorption at g=2.003 was found in Fig. 2-B, which is much stronger than that of  $SiO_2 \cdot xH_2O$ . It is possible to consider that the new site for electron trapping was produced or another type of sulfur oxide radicals was formed by  $\gamma$ -irradiation. In the sulfur oxide radicals, the  $SO_3^-$  radical has a nearly isotropic g value and shows a singlet near at g=2.003. This radical is known to be stable even at  $200^{\circ}.9^{\circ}$  The absorption intensity of the  $SO_4^-$  radicals in Fig. 2-B decreased when the sample was kept for a day at room temperature. On the contrary, the absorption at g=2.003 became stronger. It has been reported that the  $SO_4^-$  radicals formed in the sulfate by  $\gamma$ -irradiation at  $-196^{\circ}$  decomposes into the  $SO_3^-$  radicals at room temperature. From these results, the absorption at g=2.003 is attributable to the  $SO_3^-$  radicals. The radicals did not decay by heat-treatment at  $100^{\circ}$  for 7 hours. The adsorbed  $H_2O$  makes the formation of the  $SO_3^-$  radicals difficult is consistent with the fact that the  $SO_3^-$  radicals were not found in  $\gamma$ -irradiated aqueous sulfuric acid glasses.

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